

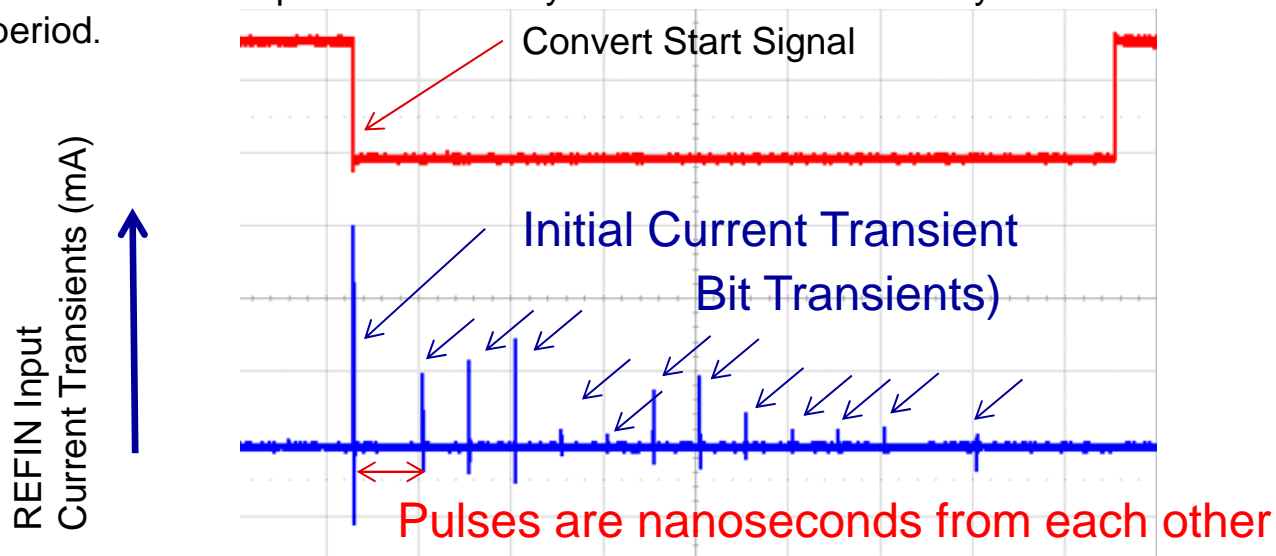
Optimal Voltage Reference Design for SAR ADCs

Luis Chioye – Precision Data Converters

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SAR ADC Architecture

- The Reference is sampled several times during each conversion
- High-current transients (~10's mA range) are present in this REF input where the ADC's internal capacitor array is switched and charged as the bit decisions are made as binary weighted bit conversions are made.
- Current transient pulses occur only a few nanoseconds away of each other during the conversion period.



ADS8881 Reference Bypass capacitor

- 10uF to 22μF range
- Ceramic X7R-grade, 0805-size, > 10-V rating
- Place right at the REFIN pin, use wide, low inductance connections
- **Follow datasheet recommendations**

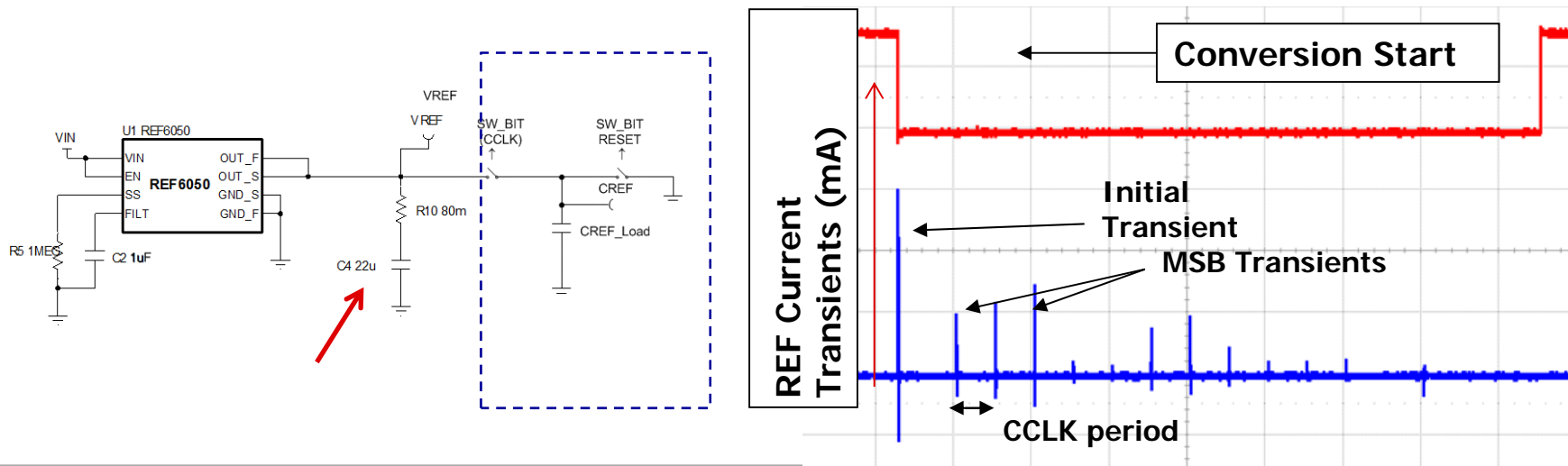
ADS8881:18-Bit, 1-MSPS, SAR ADC:

EXTERNAL REFERENCE INPUT					
V _{REF}	Input range	ADS8881C	3	5	V
		ADS8881I	2.5	5	
	Reference input current	During conversion, 1-MHz sample rate, mid-code	300		μA
	Reference leakage current		250		nA
C _{REF}	Decoupling capacitor at the REF input		10	22	μF
	Input leakage current	During acquisition for dc input	5		nA

High-performance (16-Bit) often require $C_{REF} \geq 10\mu\text{F}$

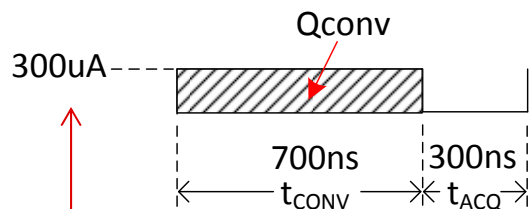
Reference Bypass capacitor

- Why is the large reference bypass capacitor required?
 - Works as large charge bucket
 - Provides instantaneous charge at MSBs decisions
 - Fast Transients are separated by CCLK period (10's ns)
 - Reference droop must be less $< \frac{1}{2}$ LSB between CCLKs



Reference Bypass capacitor

- Why is the large reference bypass capacitor required?
 - For example, ADS8881, 18-B, 1-MSPS, SAR ADC:



Datasheet
Average REFIN Current

$$Q = I * t$$

$$I_{conv} = 300 \mu A$$

$$t_{conv} = 700 ns$$

$$Q_{conv} = 300 \mu A * 700 ns = 210 pC$$

REFIN charge during each conversion

Charge/current during MSB bit decision

$$Q_{CONV} = Q_{MSB} + Q_{LSBs}$$

$$Q_{MSB} = \frac{1}{2} Q_{CONV} = \frac{210 pC}{2} = 105 pC$$

$$t_{CCLK} = \frac{700 ns}{18_{CCLKs}} \approx 40 ns \rightarrow \text{Conversion Clock}$$

$$I = \frac{Q}{t_{CCLK}} = \frac{105 pC}{40 ns} = 2.63 mA$$

Reference Bypass capacitor

- Why is the large reference bypass capacitor required?
 - For example, ADS8881, 18-B, 1-MSPS, SAR ADC:

**For this approximate calculation,
Assume most charge from bypass Capacitor and
keep VREF voltage droop <1/4 LSB**

$$I_C = C \frac{dV}{dt}$$
$$LSB = 38.14\mu V \rightarrow \begin{array}{l} \text{18-B ADC} \\ \text{Full-Scale}=\pm 5V \end{array}$$
$$dV = \frac{1}{4} LSB = 9.53\mu V$$
$$dt = t_{CLK} = 40ns \rightarrow \begin{array}{l} \text{Conversion} \\ \text{Clock} \end{array}$$
$$C = I_C \frac{dt}{dV} = 2.63mA \cdot \frac{40ns}{9.53\mu V} \approx 11.04\mu F$$

Datasheet recommends 10 μ F - 22 μ F

ADS8881

Build TINA REF Input Model for a SAR

Important Datasheet Parameters

Example: ADS8881 18-B, 1-MSPS, Fully-Differential Input ADC

Sampling Rate = 1-MSPS
 Throughput Period: $t_{\text{cycle}}=1\mu\text{s}$
 Conversion Time: $t_{\text{conv}}=710\text{ns}$ (max)
 Input Equivalent Circuit: $R_{\text{SH}} / C_{\text{SH}}$

$V_{\text{REF}} = 5\text{V}$
 Fully-Differential Input ADC
 Full-scale Range: $\pm V_{\text{REF}} = \pm 10\text{V}$
 ADC Resolution / Least Significant Bit (LSB):

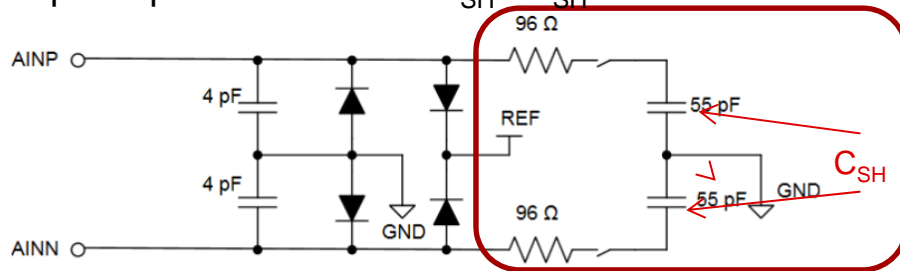


Figure 47. Input Sampling Stage Equivalent Circuit

$$LSB = \frac{\pm V_{\text{REF}}}{2^N} = \frac{2 \cdot V_{\text{REF}}}{2^{18}} = 38.14 \mu\text{V}$$

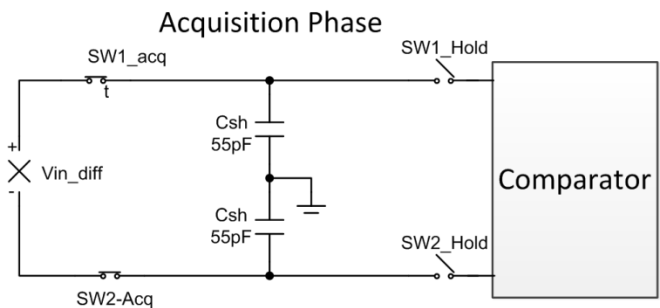
$$\frac{1}{2} LSB = 19.07 \mu\text{V}$$

'Average' Reference Input Current
 At Full throughput

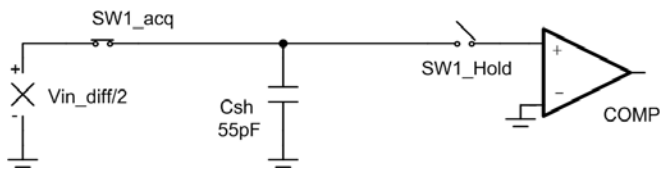
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TEXAS INSTRUMENTS

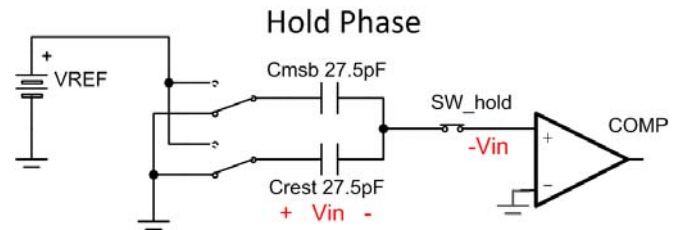
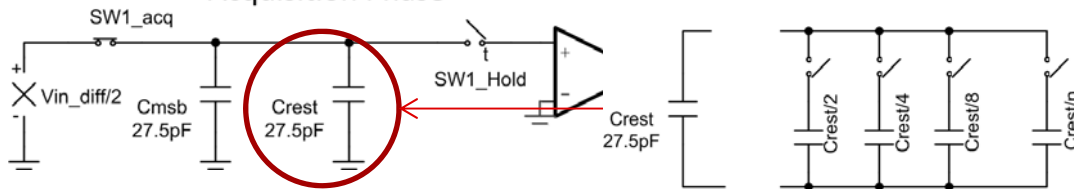
Estimate REFIN Capacitive Load:



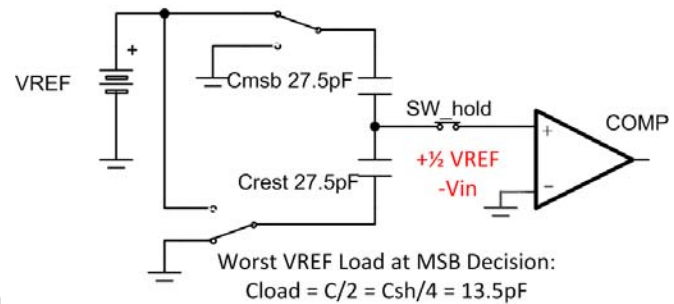
↓ Simplify/Redraw as SE circuit
Acquisition Phase



↓ Acquisition Phase



MSB bit Decision



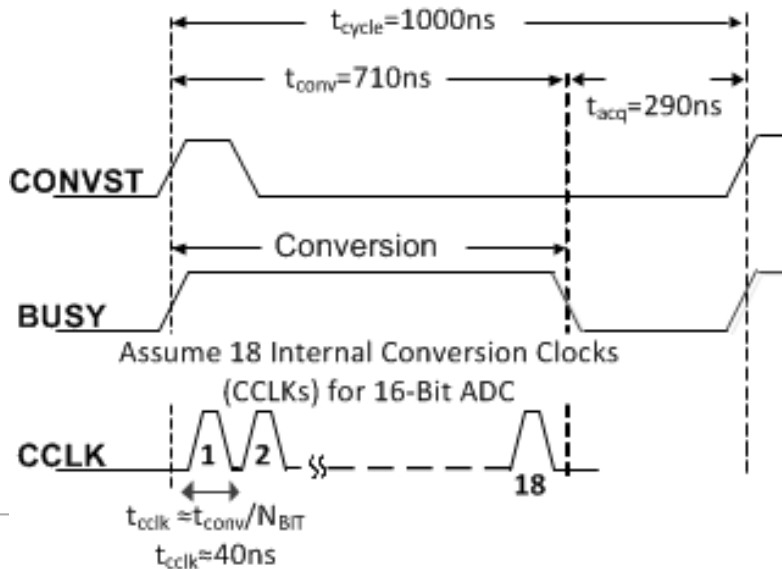
NOTE: REFIN Cmsb not always 1/4 Csh; depends on device Architecture!! This is a first order estimate.

Conversion Period and Conversion Clock Timing

ADS8881 uses an internal conversion clock (CCLK) Datasheet Specifies t_{conv} max

SAMPLING DYNAMICS				
t_{conv}	Conversion time		500	710 ns
t_{ACQ}	Acquisition time		290	ns
	Maximum throughput rate with or without latency		1000	kHz

Estimate internal Conversion Clock period



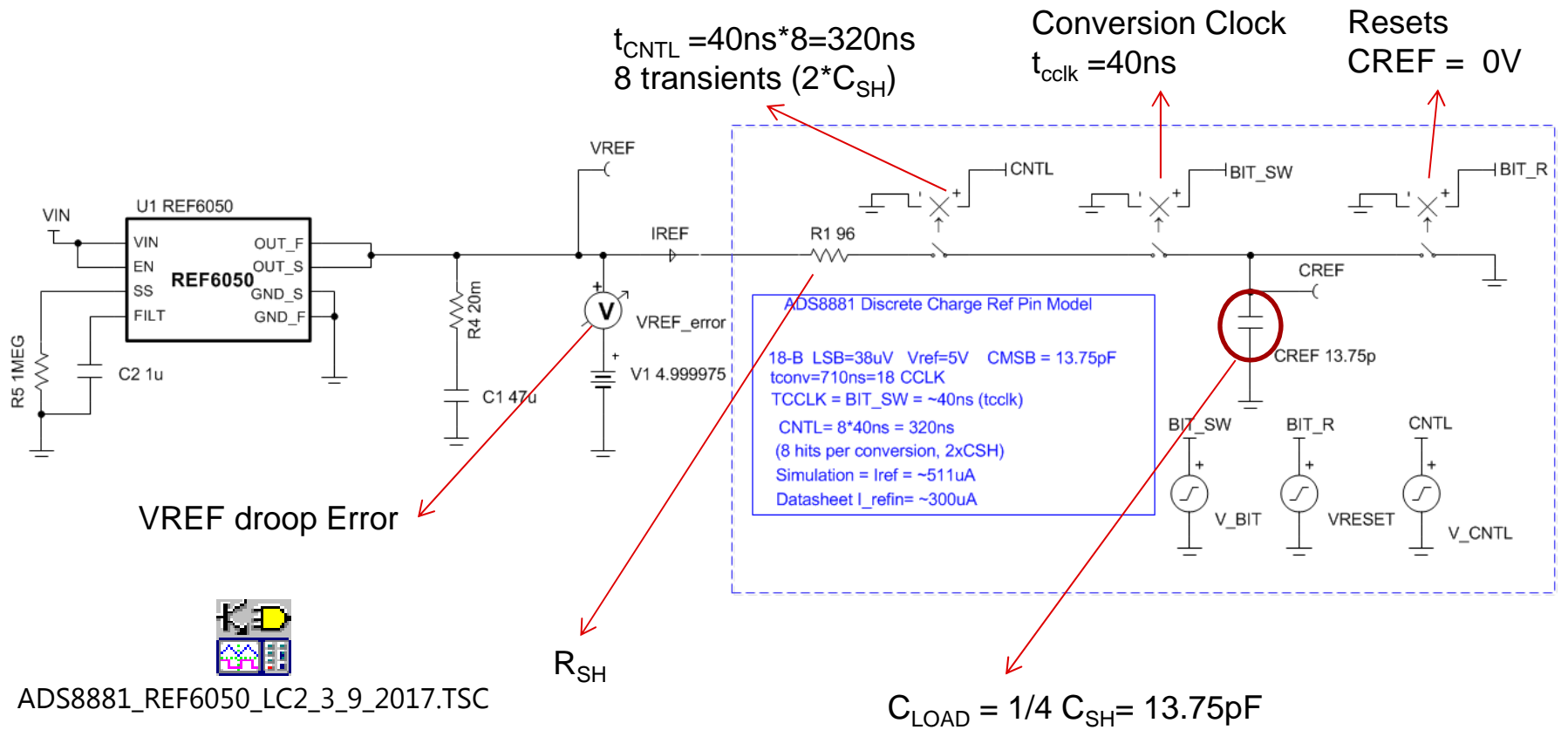
$$F_{sample} = 1000kHz$$

$$t_{cycle} = \frac{1}{1000kHz} = 1\mu s$$

$$t_{conv} = 710ns$$

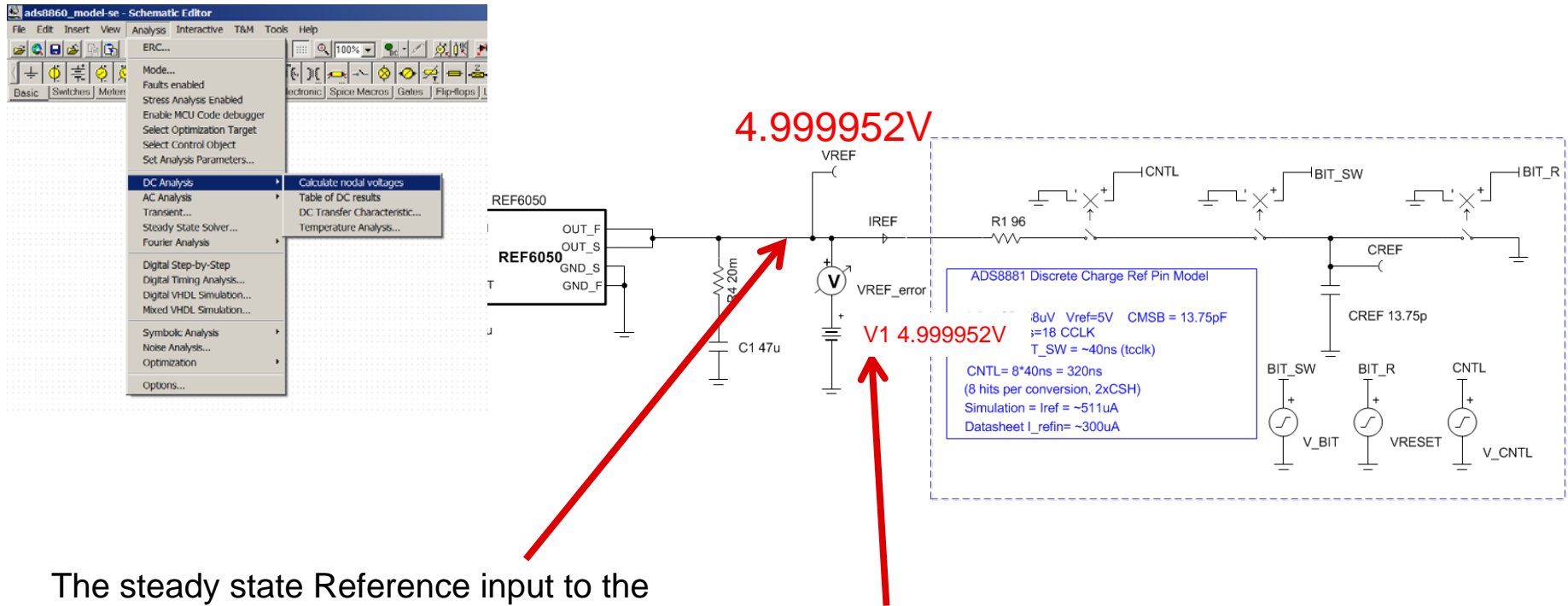
$$t_{cclk} \approx \frac{t_{conv}}{N_{BIT}} = \frac{710ns}{18} \approx 40ns$$

TINA SPICE Equivalent Model



ADS8881_REF6050_LC2_3_9_2017.TSC

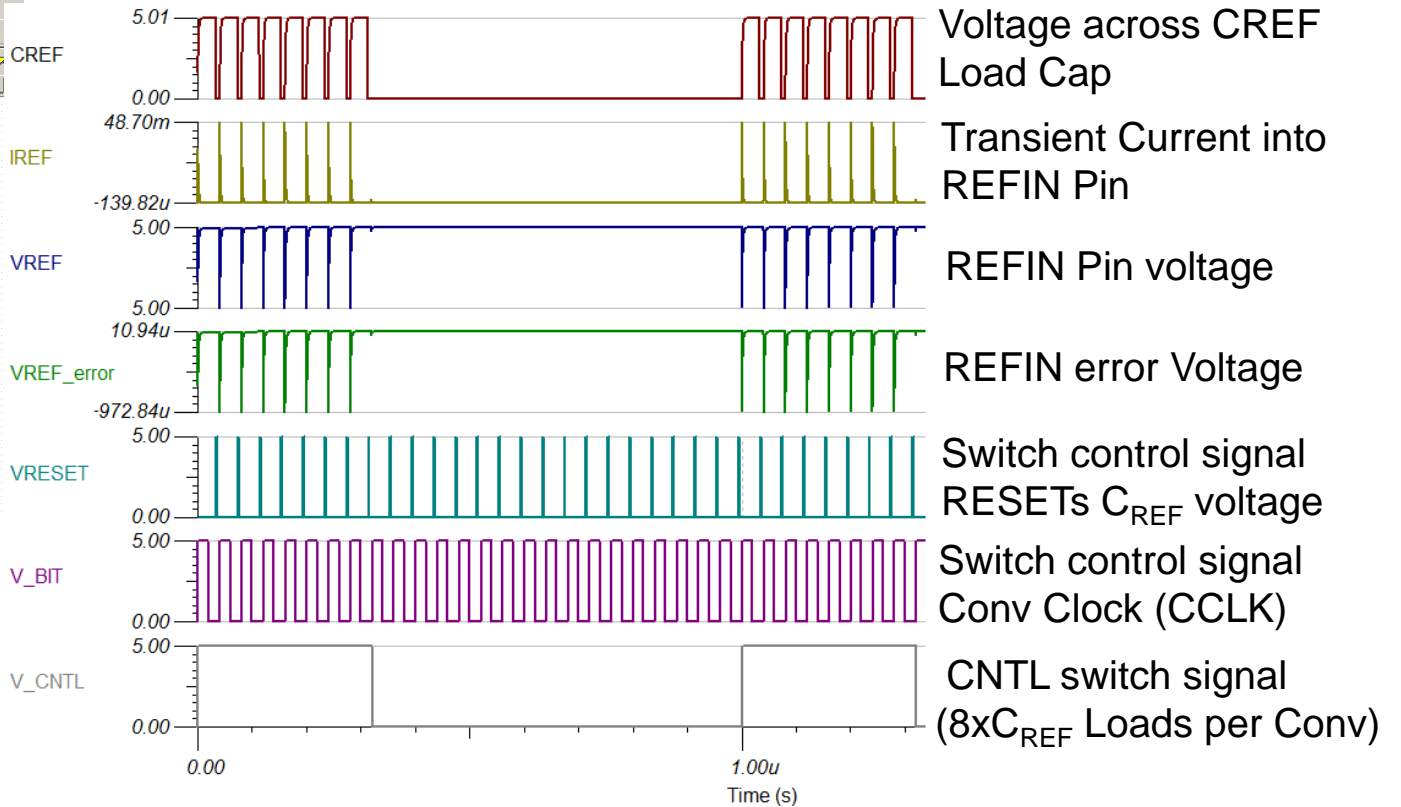
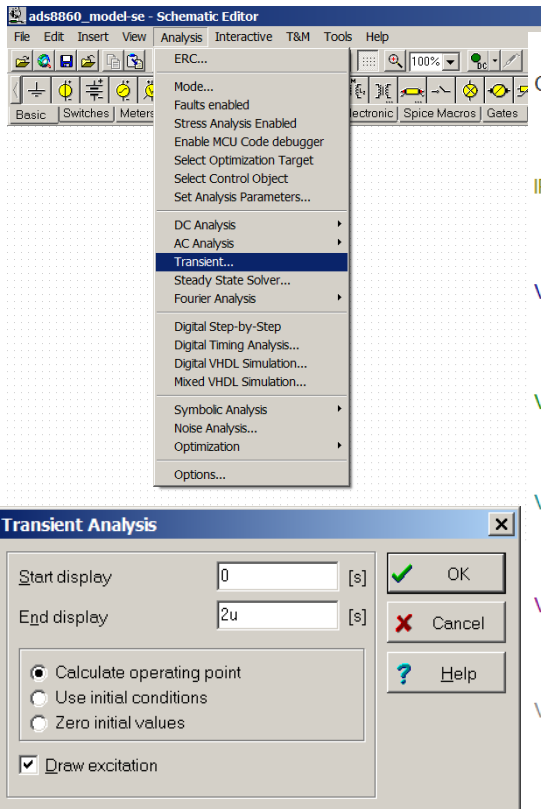
Steady state Simulation Results



The steady state Reference input to the includes DC external reference initial accuracy error.

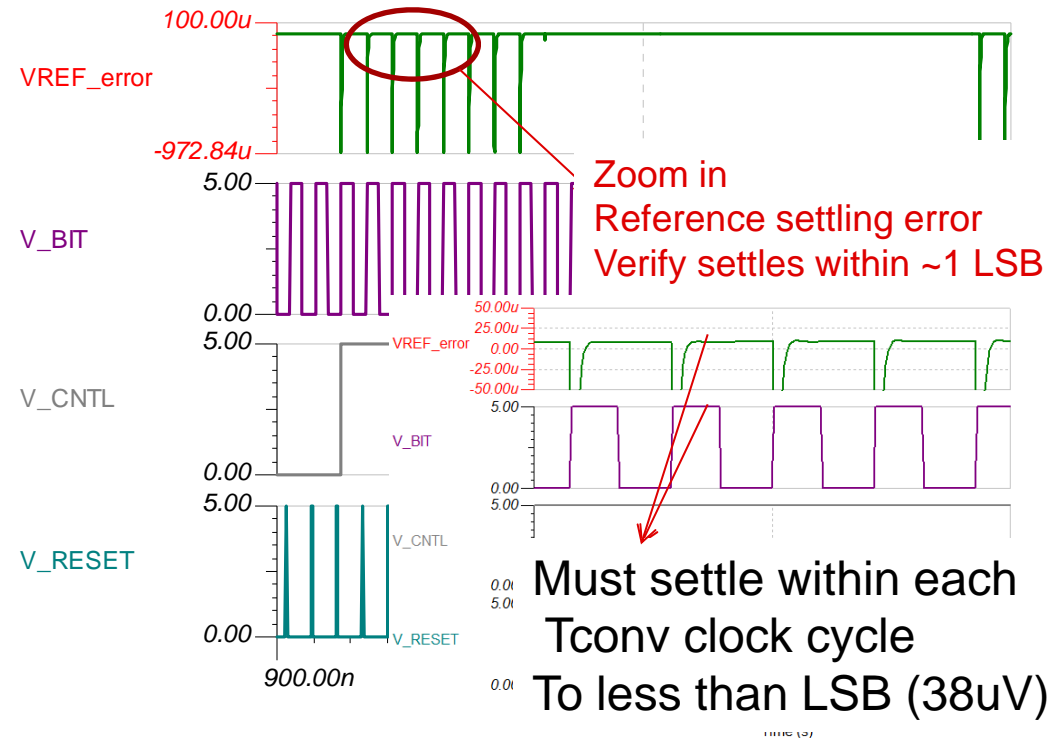
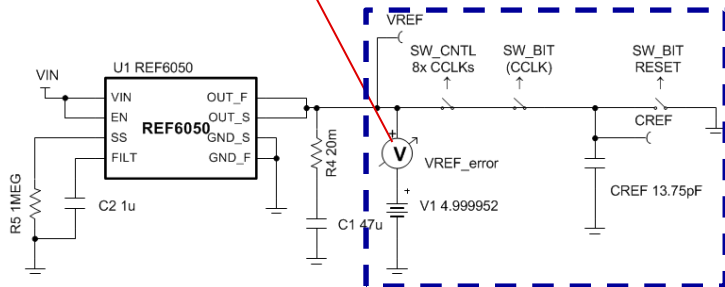
Set the Reference input source to match the steady state Reference input.

Example simulation: transient results



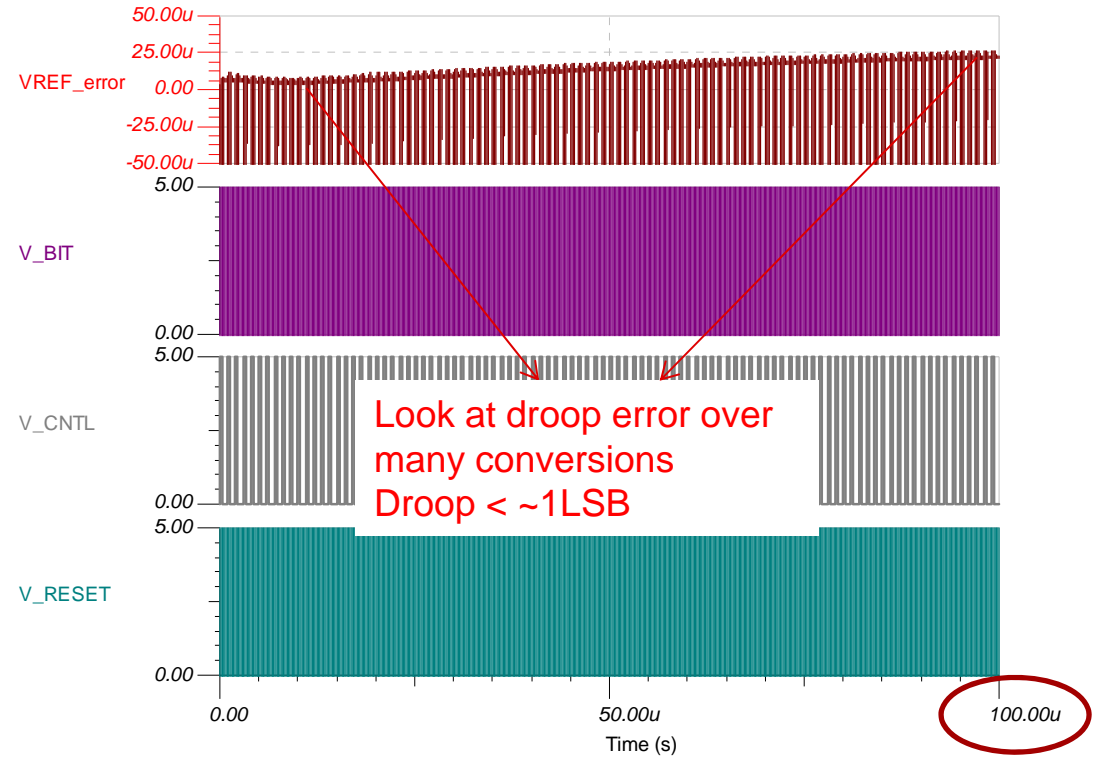
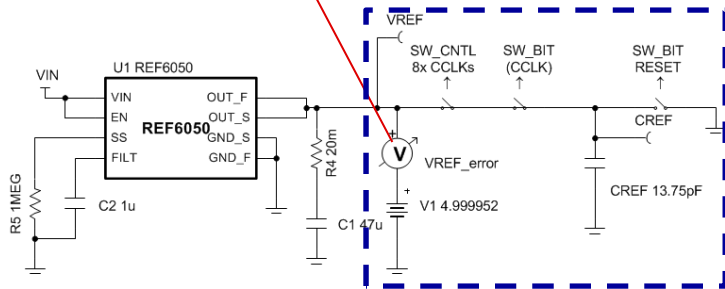
Key Result: Error Signal

Check Settling



Key Result: Error Signal

Check Settling



Average Current in Simulation

Average Current over the conversion cycle is $529\mu\text{A}$ in approximate TINA simulation model (conservative)

Datasheet spec is $300\mu\text{A}$

